

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of :  
Hiroyuki FURUYA, et al. :  
Serial No.: Continuation of Application No. :  
PCT/JP02/13350 : Group Art Unit:  
Filed: July 17, 2003 : Examiner:  
For: METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE  
AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Prior to examination of the above-referenced application, please amend the application as follows: